CHENMKO ENTERPRISE CO.,LTD

CHT5401WPT

Lead free devices

SURFACE MOUNT
PNP SILICON Transistor

VOLTAGE 150 Volts CURRENT 0.2 Ampere

APPLICATION

* Telephony and proferssional communction equipment.
* Other switching applications.

FEATURE

* Small surface mounting type. (SC-70/SOT-323)
* Suitable for high packing density.

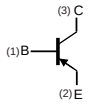
CONSTRUCTION

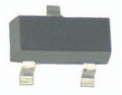
* PNP transistors in one package.

MARKING

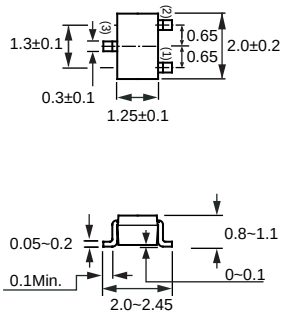
* CW

CIRCUIT





SC-70/SOT-323



Dimensions in millimeters

SC-70/SOT-323

LIMITING VALUES

In accordance with the Absolute Maximum Rating System (IEC 60134).

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
V_{CBO}	collector-base voltage	open emitter	–	-160	V
V_{CEO}	collector-emitter voltage	open base	–	-150	V
V_{EBO}	emitter-base voltage	open collector	–	-5.0	V
I_C	collector current (DC)		–	-200	mA
P_{tot}	total power dissipation	$T_{amb} \leq 25$ °C; note 1	–	0.2	W
T_{stg}	storage temperature		–65	+150	°C
T_j	junction temperature		–	150	°C
T_{amb}	operating ambient temperature		–65	+150	°C

Note

1. Transistor mounted on an FR4 printed-circuit board.

RATING CHARACTERISTIC CURVES (CHT5401WPT)

THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
$R_{th\ j\text{-}a}$	thermal resistance from junction to ambient	note 1	420	K/W

Note

1.Transistor mounted on an FR4 printed-circuit board.

CHARACTERISTICS

T_{amb} = 25 °C unless otherwise speciÞed.

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
I_{CBO}	collector cut-off current	V_{CB} = -120 V	–	-50	nA
I_{EBO}	emitter cut-off current	V_{EB}=3.0V	–	-50	nA
h_{FE}	DC current gain	I_C = -1.0 mA; V_{CE} = -5V I_C = -10mA; V_{CE} = -5V I_C = -50 mA; V_{CE} = -5V	50 60 50	– 240 –	
V_{CEsat}	collector-emitter saturation voltage	I_C = -10 mA; I_B = -1.0 mA	–	-0.2	V
		I_C = -50 mA; I_B = -5.0 mA	–	-0.5	V
V_{BEsat}	base-emitter saturation voltage	I_C =-10mA; I_B=-1.0mA	–	-1.0	V
		I_C = -50 mA; I_B = -5.0 mA	–	-1.0	V
C_{ob}	collector capacitance	$I_E = i_e$ = 0; V_{CB} = - 1 0 V; f = 1 MHz	–	6.0	pF
hfe		V_{CE}=-10V,I_C=-1.0mA,f=1.0KHz	40	200	
f_T	transition frequency	I_C =- 50 mA; V_{CE} = 1 0 V; f = 100 MHz	100	300	MHz
F	noise Þgure	I_C = 200 µA; V_{CE}= 5 V; R_S = 1 0 Ω; f =10Hz to 15.7KHz	–	8.0	dB